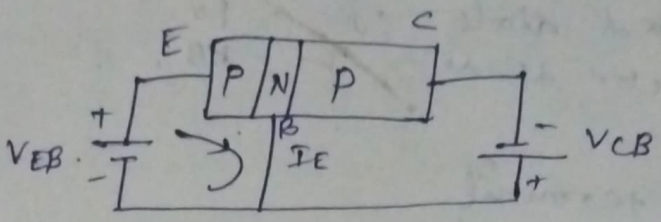
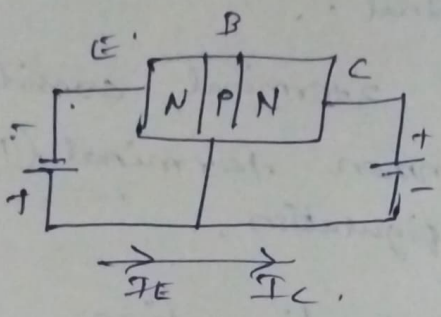
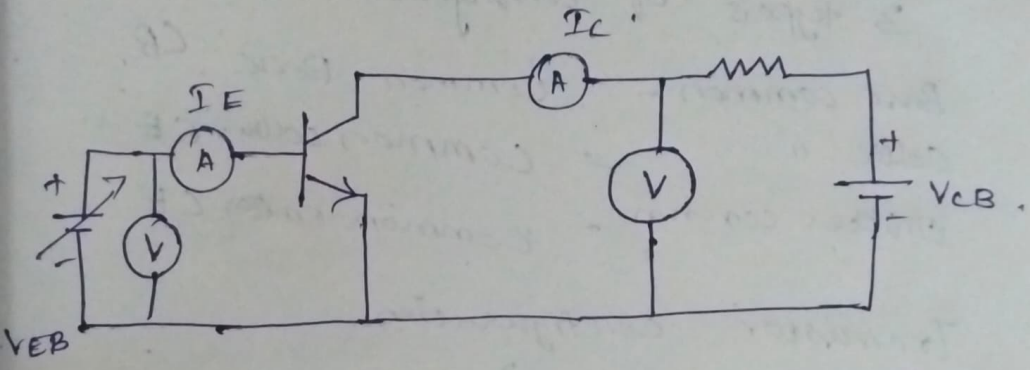
PNP transistor:



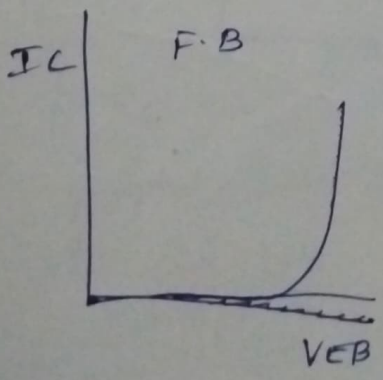




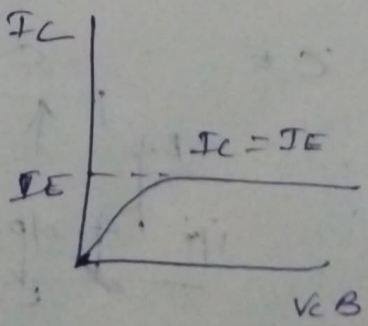
VEB More than Neo voltage. when emitter diode start conducting where VCB increases IC increases.

where IC = IE.

Emitter-Base:



Collector-Base:



Different configurations of Transistor.

Emitted diode Jun : FB.
Collector diode Jn : RB.

I/p - 2 terminal
O/p - 2 terminal.

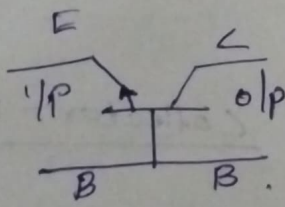
Transistor have 3 terminal considering one as common terminal (I/p, O/p) called as configuration.

3 types of configuration.

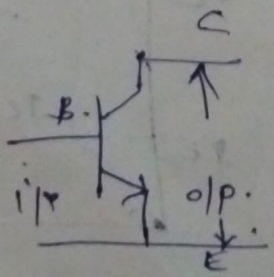
Base common :- common Base. CB
Collec " - common collec CE
Emitter common - common emitter CE

Transistor configuration
(CB, CE, CC)

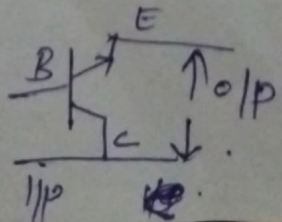
1). CB - common Base :



iii) CE

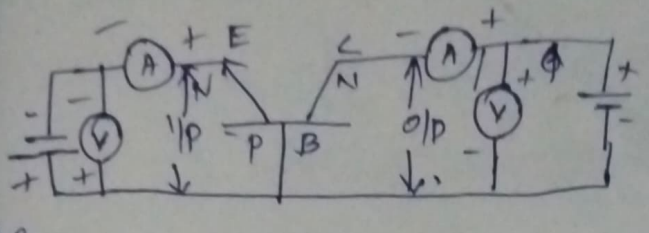


(iii) CC :



CB : NPN.

E ter - FB. Nat
C ter - RB. + very



i/p circuit:

E & B. i/p current $A_1 = I_E$

i/p voltage $V_1 = V_{EB}$

o/p circuit:

C & B

o/p current $A_2 = I_C$.

o/p voltage $V_2 = V_{CB}$.

i/p characteristic:

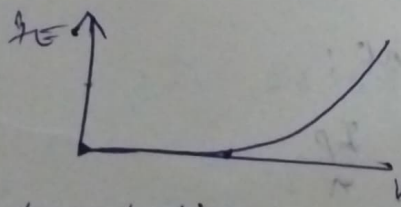
graph between i/p voltge and i/p current when o/p voltage constant.

V_{EB} Vs I_E at V_{CB} constant

emitter diode FB

when

V_{EB} > . new voltage, then i/p current I_E flows.



o/p characteristics.

graphs between o/p voltage and o/p current when i/p current constant.

V_{CB} Vs I_C with I_E constant.

o/p. o/p. i/p.

where,